

# RJK6012DPE

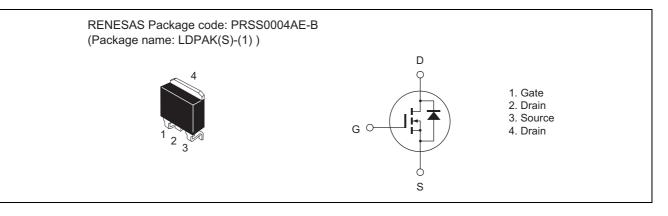
Silicon N Channel MOS FET High Speed Power Switching

> REJ03G1481-0200 Rev.2.00 Oct 16, 2006

# Features

- Low on-resistance
- Low leakage current
- High speed switching

# Outline



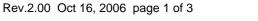
# **Absolute Maximum Ratings**

 $(Ta = 25^{\circ}C)$ Item Symbol Ratings Unit Drain to source voltage V<sub>DSS</sub> 600 V V Gate to source voltage V<sub>GSS</sub> ±30 10 A Drain current  $I_D$ Note1 Drain peak current 20 А Body-drain diode reverse drain current  $I_{DR}$ 10 А Body-drain diode reverse drain peak current 20 А I<sub>DR (pulse)</sub> I<sub>AP</sub><sup>Note3</sup> Avalanche current 3 A E<sub>AR</sub><sup>Note3</sup> 0.49 Avalanche energy mJ Pch Note2 W Channel dissipation 100 Channel to case thermal impedance θch-c 1.25 °C/W Channel temperature Tch 150 °C °C Storage temperature Tstg -55 to +150

Notes: 1.  $PW \le 10 \ \mu s$ , duty cycle  $\le 1\%$ 

2. Value at Tc = 25°C

3. STch =  $25^{\circ}$ C, Tch  $\leq 150^{\circ}$ C





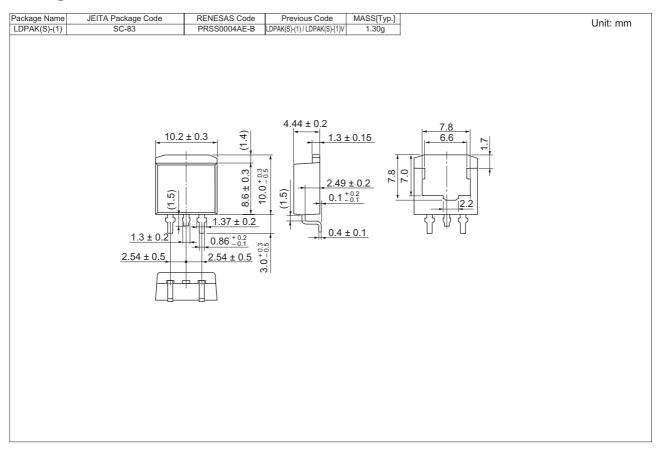
# **Electrical Characteristics**

						$(Ta = 25^{\circ}C)$
ltem	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	V <sub>(BR)DSS</sub>	600	—	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero gate voltage drain current	I <sub>DSS</sub>	_	—	1	μΑ	$V_{DS} = 600 \text{ V}, V_{GS} = 0$
Gate to source leak current	I <sub>GSS</sub>		—	±0.1	μΑ	$V_{GS}=\pm 30~V,~V_{DS}=0$
Gate to source cutoff voltage	V <sub>GS(off)</sub>	3.0	—	4.5	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Static drain to source on state resistance	R <sub>DS(on)</sub>		0.77	0.92	Ω	$I_D = 5 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$
Input capacitance	Ciss	_	1100	_	pF	V <sub>DS</sub> = 25 V
Output capacitance	Coss	_	110	_	pF	V <sub>GS</sub> = 0 f = 1 MHz
Reverse transfer capacitance	Crss		13	_	pF	
Turn-on delay time	t <sub>d(on)</sub>		30		ns	I <sub>D</sub> = 5 A
Rise time	tr	_	22	—	ns	V <sub>GS</sub> = 10 V
Turn-off delay time	t <sub>d(off)</sub>	_	80	—	ns	$R_{L} = 60 \Omega$ $Rg = 10 \Omega$
Fall time	t <sub>f</sub>	_	17	—	ns	
Total gate charge	Qg		30	—	nC	V <sub>DD</sub> = 480 V
Gate to source charge	Qgs	_	6.5	—	nC	V <sub>GS</sub> = 10 V I <sub>D</sub> = 10 A
Gate to drain charge	Qgd	—	14.5	—	nC	
Body-drain diode forward voltage	V <sub>DF</sub>	—	0.88	1.50	V	$I_F = 10 \text{ A}, V_{GS} = 0^{Note4}$
Body-drain diode reverse recovery time	t <sub>rr</sub>	_	350	_	ns	I <sub>F</sub> = 10 A, V <sub>GS</sub> = 0 di <sub>F</sub> /dt = 100 A/μs

Notes: 4. Pulse test



# **Package Dimensions**



# **Ordering Information**

Part Name	Quantity	Shipping Container
RJK6012DPE-00-J3	1000 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.



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